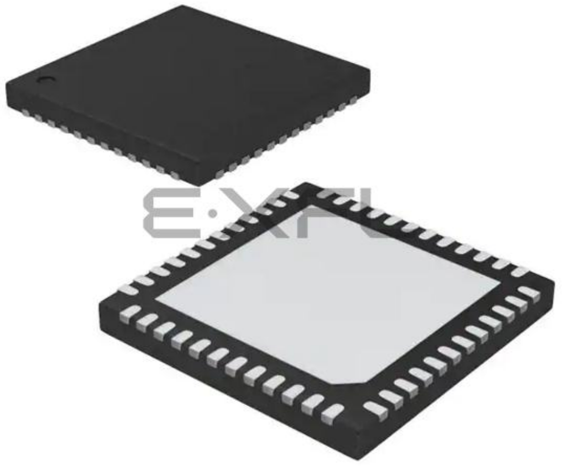
Microchip Technology - A3P030-QNG48 Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	34
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p030-qng48

Table 2-9 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard Plus I/O Banks

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
2.5 V LVCMOS	2.5	–	5.14
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.48
3.3 V PCI	3.3	–	18.13
3.3 V PCI-X	3.3	–	18.13

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-10 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard I/O Banks

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	17.24
3.3 V LVCMOS Wide Range[3]	3.3	–	17.24
2.5 V LVCMOS	2.5	–	5.19
1.8 V LVCMOS	1.8	–	2.18
1.5 V LVCMOS (JESD8-11)	1.5	–	1.52

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-22 • **Summary of AC Measuring Points**

Standard	Measuring Trip Point (V_{trip})
3.3 V LVTTL / 3.3 V LVCMOS	1.4 V
3.3 V LVCMOS Wide Range	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
3.3 V PCI	0.285 * VCCI (RR)
	0.615 * VCCI (FF)
3.3 V PCI-X	0.285 * VCCI (RR)
	0.615 * VCCI (FF)

Table 2-23 • **I/O AC Parameter Definitions**

Parameter	Parameter Definition
t_{DP}	Data to Pad delay through the Output Buffer
t_{PY}	Pad to Data delay through the Input Buffer
t_{DOUT}	Data to Output Buffer delay through the I/O interface
t_{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer to Data delay through the I/O interface
t_{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t_{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t_{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t_{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t_{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t_{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

Timing Characteristics

Table 2-50 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.60	11.84	0.04	1.02	0.43	11.84	10.00	4.10	4.04	15.23	13.40	ns
		–1	0.51	10.07	0.04	0.86	0.36	10.07	8.51	3.48	3.44	12.96	11.40	ns
		–2	0.45	8.84	0.03	0.76	0.32	8.84	7.47	3.06	3.02	11.38	10.00	ns
100 µA	6 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	8 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	12 mA	Std.	0.60	5.46	0.04	1.02	0.43	5.46	4.29	4.97	5.54	8.86	7.68	ns
		–1	0.51	4.65	0.04	0.86	0.36	4.65	3.65	4.22	4.71	7.53	6.54	ns
		–2	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
100 µA	16 mA	Std.	0.60	5.15	0.04	1.02	0.43	5.15	3.89	5.04	5.69	8.55	7.29	ns
		–1	0.51	4.38	0.04	0.86	0.36	4.38	3.31	4.29	4.84	7.27	6.20	ns
		–2	0.45	3.85	0.03	0.76	0.32	3.85	2.91	3.77	4.25	6.38	5.44	ns
100 µA	24 mA	Std.	0.60	4.75	0.04	1.02	0.43	4.75	3.22	5.14	6.28	8.15	6.61	ns
		–1	0.51	4.04	0.04	0.86	0.36	4.04	2.74	4.37	5.34	6.93	5.62	ns
		–2	0.45	3.55	0.03	0.76	0.32	3.55	2.40	3.84	4.69	6.09	4.94	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-51 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	0.60	15.86	0.04	1.54	0.43	15.86	13.51	4.09	3.80	19.25	16.90	ns
		–1	0.51	13.49	0.04	1.31	0.36	13.49	11.49	3.48	3.23	16.38	14.38	ns
		–2	0.45	11.84	0.03	1.15	0.32	11.84	10.09	3.05	2.84	14.38	12.62	ns
100 µA	4 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 µA	6 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 µA	8 mA	Std.	0.60	8.63	0.04	1.54	0.43	8.63	7.39	4.96	5.28	12.02	10.79	ns
		–1	0.51	7.34	0.04	1.31	0.36	7.34	6.29	4.22	4.49	10.23	9.18	ns
		–2	0.45	6.44	0.03	1.15	0.32	6.44	5.52	3.70	3.94	8.98	8.06	ns
100 µA	16 mA	Std.	0.60	8.05	0.04	1.54	0.43	8.05	6.93	5.03	5.43	11.44	10.32	ns
		–1	0.51	6.85	0.04	1.31	0.36	6.85	5.90	4.28	4.62	9.74	8.78	ns
		–2	0.45	6.01	0.03	1.15	0.32	6.01	5.18	3.76	4.06	8.55	7.71	ns
100 µA	24 mA	Std.	0.60	7.50	0.04	1.54	0.43	7.50	6.90	5.13	6.00	10.89	10.29	ns
		–1	0.51	6.38	0.04	1.31	0.36	6.38	5.87	4.36	5.11	9.27	8.76	ns
		–2	0.45	5.60	0.03	1.15	0.32	5.60	5.15	3.83	4.48	8.13	7.69	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

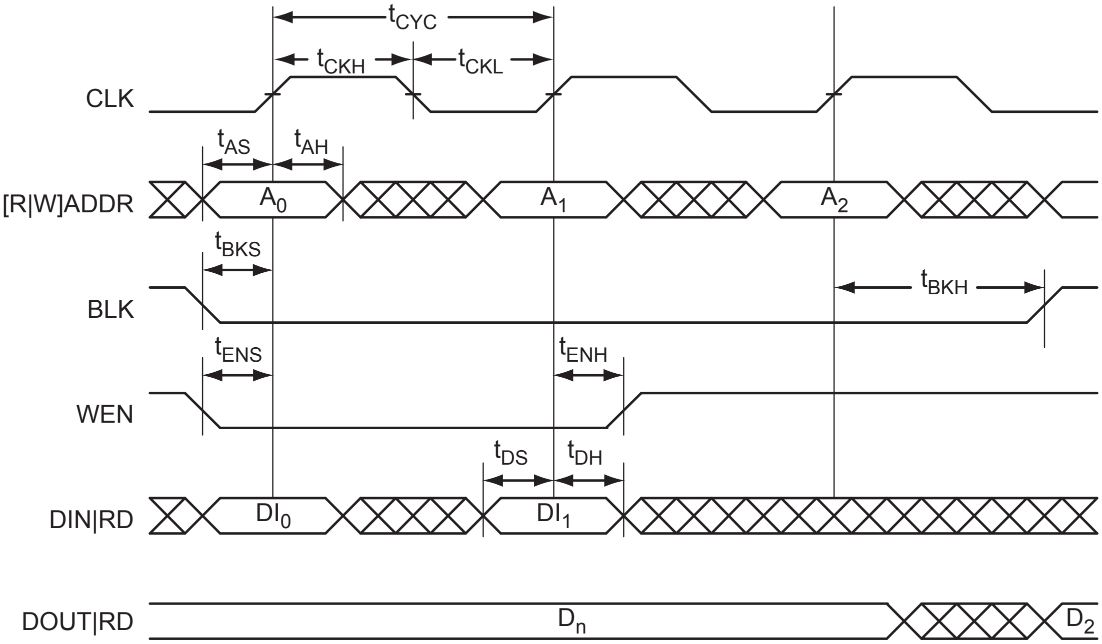

***Figure 2-33* • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**

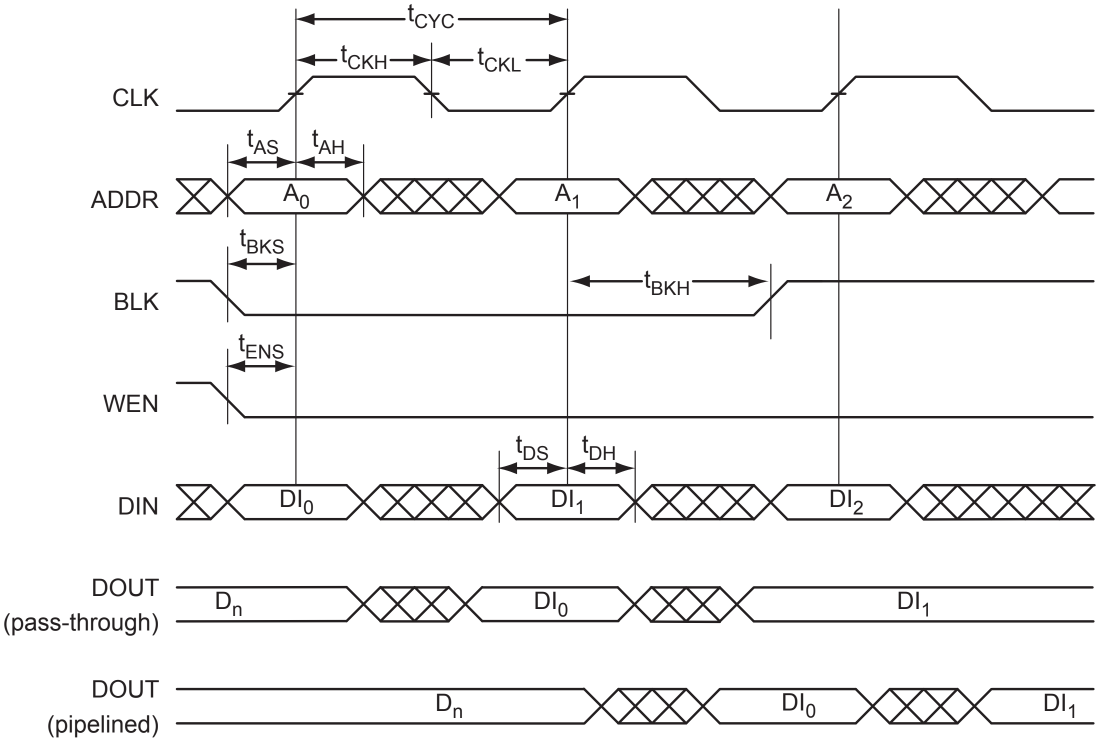

***Figure 2-34* • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 Only.**

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1